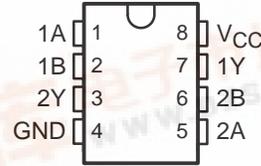


SN74LVC2G38 DUAL 2-INPUT NAND GATE WITH OPEN DRAIN OUTPUT

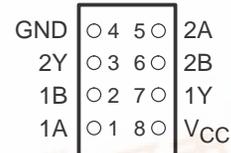
SCES554A – MARCH 2004 – REVISED OCTOBER 2004

- Available in the Texas Instruments NanoStar™ and NanoFree™ Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 4 ns at 3.3 V
- Low Power Consumption, 10-μA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) <0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) >2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DCT OR DCU PACKAGE
(TOP VIEW)



YEP OR YZP PACKAGE
(BOTTOM VIEW)



description/ordering information

The SN74LVC2G38 is designed for 1.65-V to 5.5-V V_{CC} operation.

This device is a dual two-input NAND buffer gate with open-drain outputs. It performs the Boolean function $Y = \overline{A \cdot B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

ORDERING INFORMATION

T _A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING‡
-40°C to 85°C	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Reel of 3000	SN74LVC2G38YEPR	___D7_
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC2G38YZPR	
	SSOP – DCT	Reel of 3000	SN74LVC2G38DCTR	C38_ _ _
	VSSOP – DCU	Reel of 3000 Reel of 250	SN74LVC2G38DCUR SN74LVC2G38DCUT	C38_

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

‡ DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site.

DCU: The actual top-side marking has one additional character that designates the assembly/test site.

YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

SN74LVC2G38
DUAL 2-INPUT NAND GATE
WITH OPEN DRAIN OUTPUT

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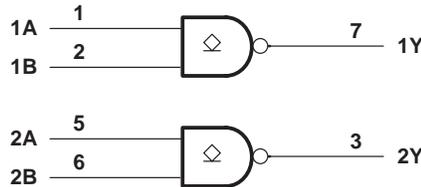
description/ordering information (continued)

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	-0.5 V to 6.5 V
Input voltage range, V_I (see Note 1)	-0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1)	-0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2)	-0.5 V to $V_{CC} + 0.5$ V
Input clamp current, I_{IK} ($V_I < 0$)	-50 mA
Output clamp current, I_{OK} ($V_O < 0$)	-50 mA
Continuous output current, I_O	±50 mA
Continuous current through V_{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DCT package	220°C/W
DCU package	227°C/W
YEP/YZP package	102°C/W
Storage temperature range, T_{stg}	-65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
 2. The value of V_{CC} is provided in the recommended operating conditions table.
 3. The package thermal impedance is calculated in accordance with JESD 51-7.

SN74LVC2G38
DUAL 2-INPUT NAND GATE
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recommended operating conditions (see Note 4)

		MIN	MAX	UNIT	
V _{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	1.7		
		V _{CC} = 3 V to 3.6 V	2		
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V		0.7	
		V _{CC} = 3 V to 3.6 V		0.8	
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}	
V _I	Input voltage	0	5.5	V	
V _O	Output voltage	0	V _{CC}	V	
I _{OL}	Low-level output current	V _{CC} = 1.65 V		4	mA
		V _{CC} = 2.3 V		8	
		V _{CC} = 3 V		16	
				24	
		V _{CC} = 4.5 V		32	
Δt/Δv	Input transition rise or fall rate	V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V _{CC} = 3.3 V ± 0.3 V		10	
		V _{CC} = 5 V ± 0.5 V		5	
T _A	Operating free-air temperature	-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP†	MAX	UNIT
V _{OL}	I _{OL} = 100 μA	1.65 V to 5.5 V			0.1	V
	I _{OL} = 4 mA	1.65 V			0.45	
	I _{OL} = 8 mA	2.3 V			0.3	
	I _{OL} = 16 mA	3 V			0.4	
					0.55	
	I _{OL} = 32 mA	4.5 V			0.55	
I _I	A or B inputs V _I = 5.5 V or GND	0 to 5.5 V			±1	μA
I _{off}	V _I or V _O = 5.5 V	0			±10	μA
I _{CC}	V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V			10	μA
ΔI _{CC}	One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μA
C _i	V _I = V _{CC} or GND	3.3 V			4	pF
C _o	V _O = V _{CC} or GND	3.3 V			4.5	pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

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DUAL 2-INPUT NAND GATE
WITH OPEN DRAIN OUTPUT

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switching characteristics over recommended operating free-air temperature range, $C_L = 15 \text{ pF}$ (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$		$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	2.5	8.5	1.5	5.2	1.3	4	0.9	3	ns

switching characteristics over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ or 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$		$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	2.8	10	1.6	6	1.4	4.5	1	3.9	ns

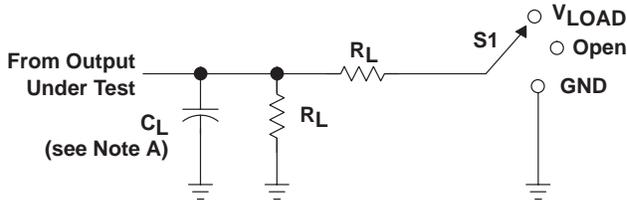
operating characteristics, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	$V_{CC} = 1.8 \text{ V}$	$V_{CC} = 2.5 \text{ V}$	$V_{CC} = 3.3 \text{ V}$	$V_{CC} = 5 \text{ V}$	UNIT
		TYP	TYP	TYP	TYP	
C_{pd} Power dissipation capacitance	$f = 10 \text{ MHz}$	6	7	7	9	pF

SN74LVC2G38 DUAL 2-INPUT NAND GATE WITH OPEN DRAIN OUTPUT

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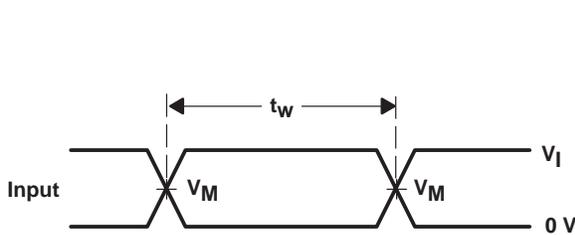
PARAMETER MEASUREMENT INFORMATION (OPEN DRAIN)



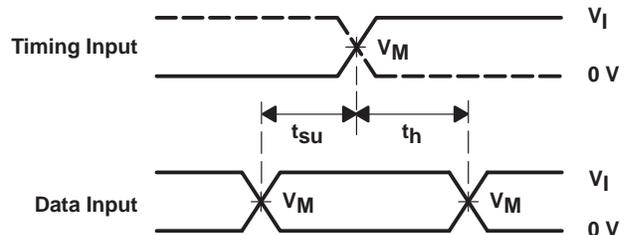
LOAD CIRCUIT

TEST	S1
tpZL (see Notes E and F)	V_{LOAD}
tpLZ (see Notes E and G)	V_{LOAD}
tPHZ/tPZH	V_{LOAD}

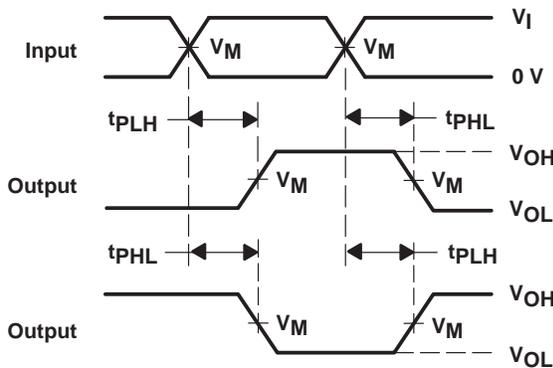
V_{CC}	INPUT		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	15 pF	1 M Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.3 V



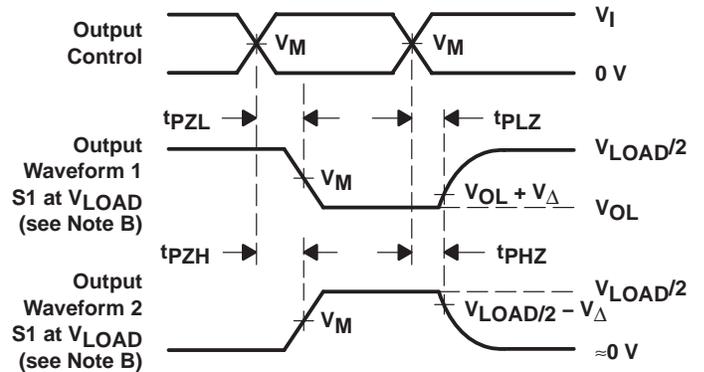
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

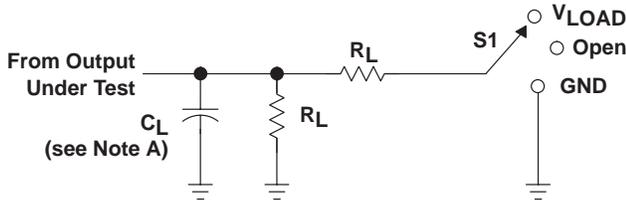
- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: PRR $\leq 10\text{ MHz}$, $Z_O = 50\ \Omega$.
 - The outputs are measured one at a time, with one transition per measurement.
 - Since this device has open-drain outputs, tPLZ and tpZL are the same as tpd.
 - tpZL is measured at V_M .
 - tpLZ is measured at $V_{OL} + V_{\Delta}$.
 - All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms

SN74LVC2G38 DUAL 2-INPUT NAND GATE WITH OPEN DRAIN OUTPUT

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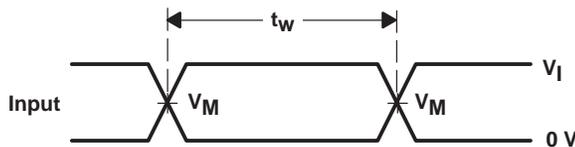
PARAMETER MEASUREMENT INFORMATION (OPEN DRAIN)



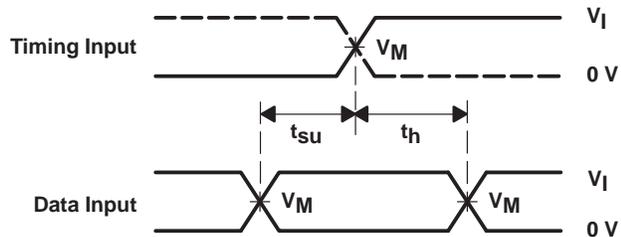
LOAD CIRCUIT

TEST	S1
t_{pZL} (see Notes E and F)	V_{LOAD}
t_{pLZ} (see Notes E and G)	V_{LOAD}
t_{PHZ}/t_{PZH}	V_{LOAD}

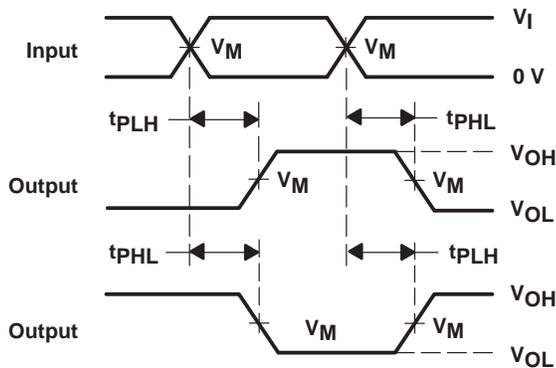
V_{CC}	INPUT		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



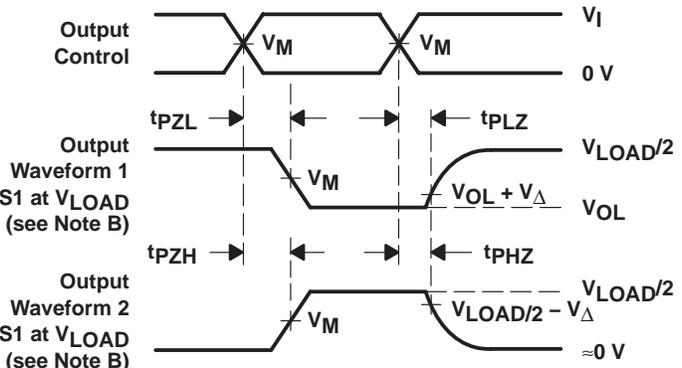
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
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VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$.
 - The outputs are measured one at a time, with one transition per measurement.
 - Since this device has open-drain outputs, t_{pLZ} and t_{pZL} are the same as t_{pd} .
 - t_{pZL} is measured at V_M .
 - t_{pLZ} is measured at $V_{OL} + V_{\Delta}$.
 - All parameters and waveforms are not applicable to all devices.

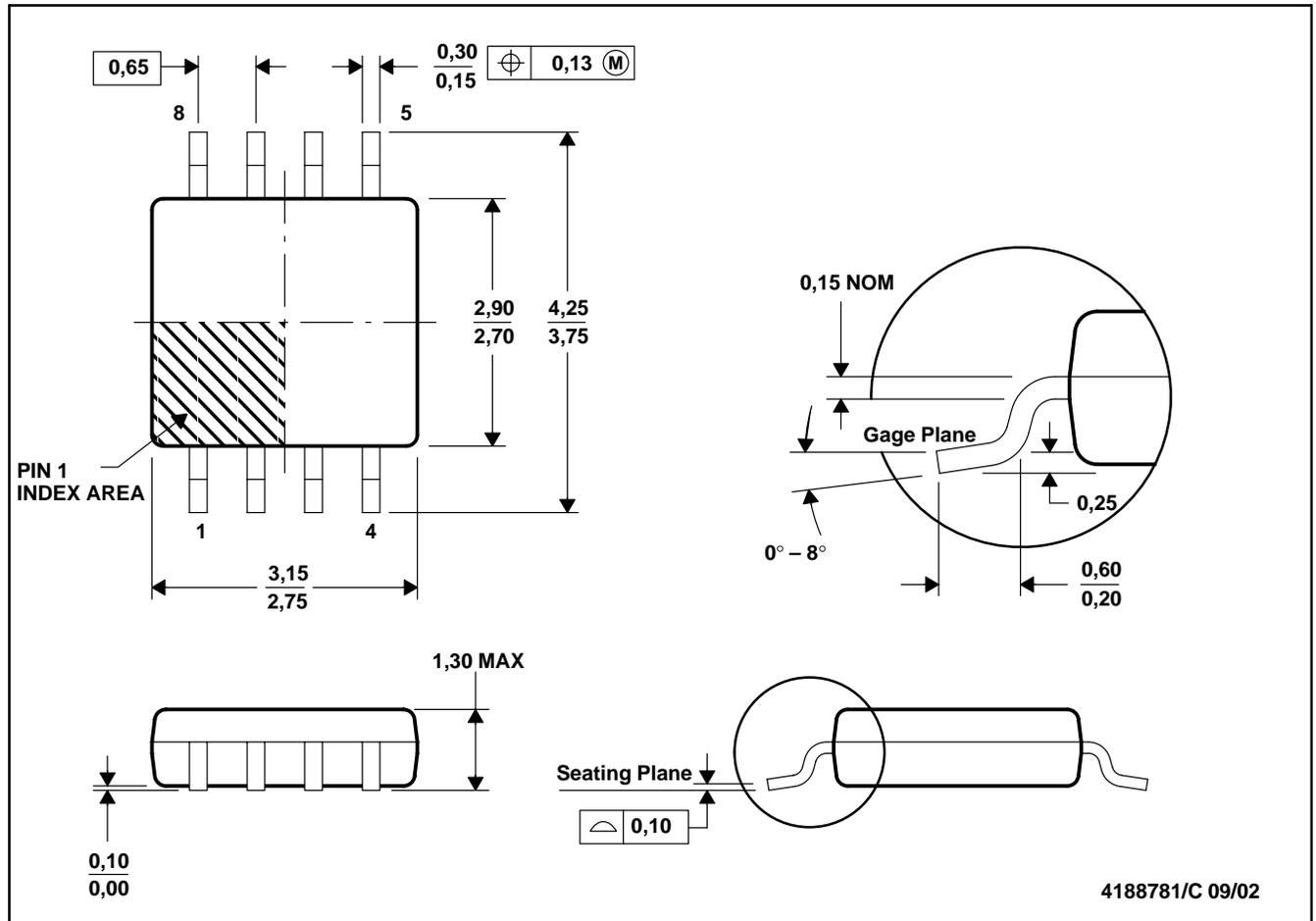
Figure 2. Load Circuit and Voltage Waveforms

MECHANICAL DATA

MPDS049B – MAY 1999 – REVISED OCTOBER 2002

DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

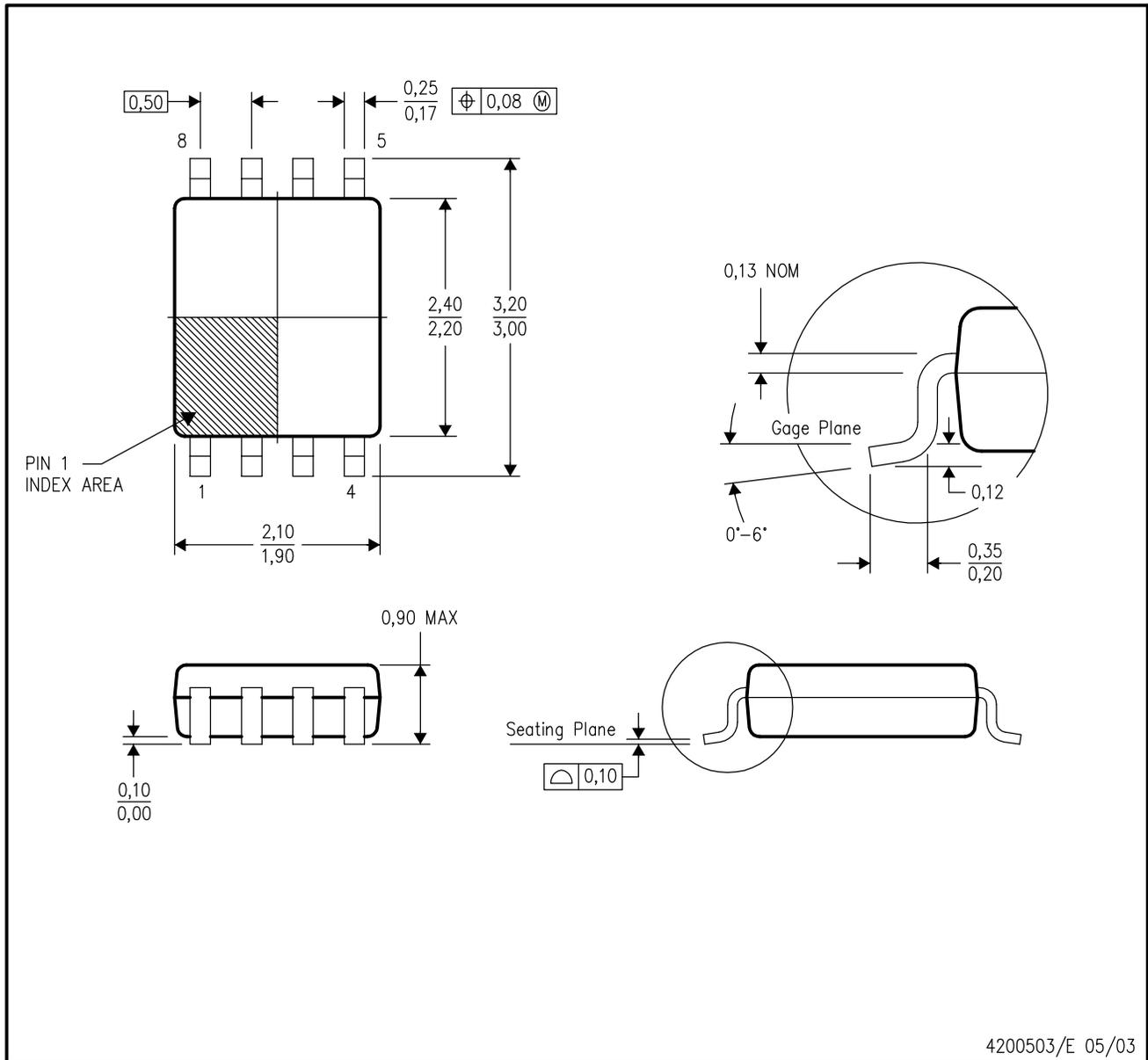


- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion
 D. Falls within JEDEC MO-187 variation DA.

MECHANICAL DATA

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



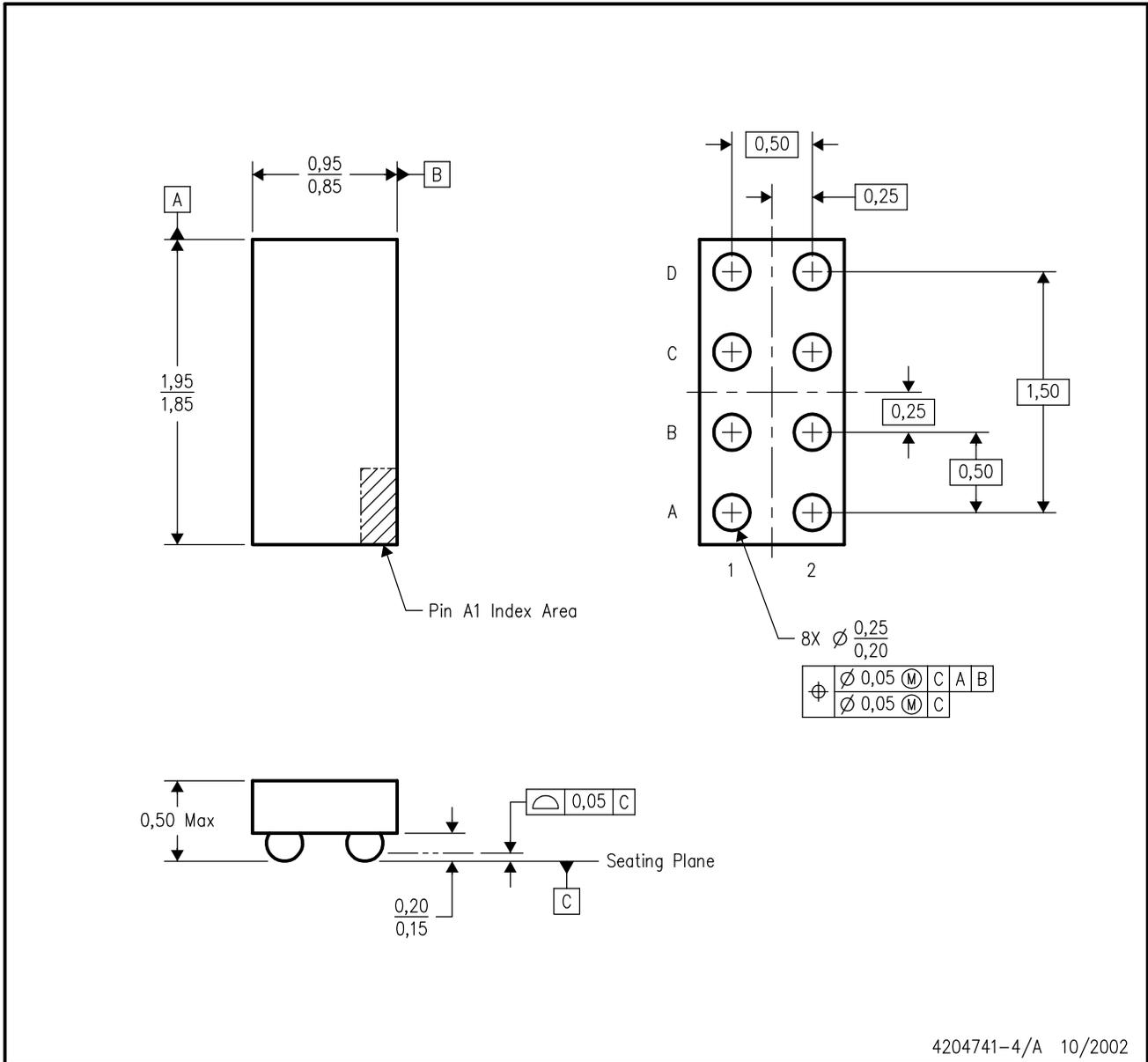
4200503/E 05/03

- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion.
 - Falls within JEDEC MO-187 variation CA.

MECHANICAL DATA

YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY

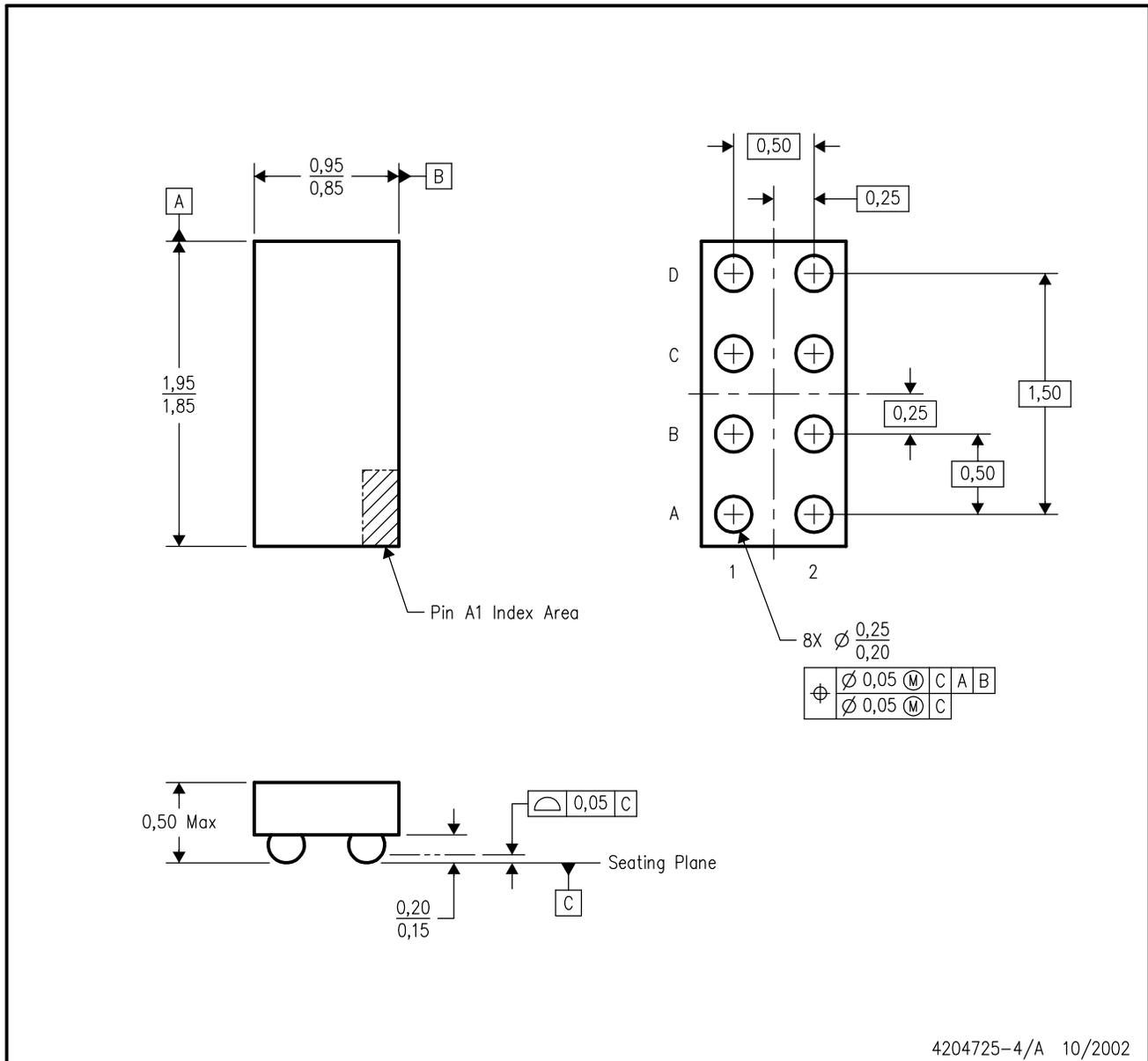


- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.
 - D. This package is lead-free. Refer to the 8 YEP package (drawing 4204725) for tin-lead (SnPb).

MECHANICAL DATA

YEP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoStar™ package configuration.
 - D. This package is tin-lead (SnPb). Refer to the 8 YZP package (drawing 4204741) for lead-free.

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